

Delocalization of tightly bound excitons in disordered systems

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Abstract

The localization length of a low energy tightly bound electron-hole pair (excitons) is calculated by exact diagonalization for small interacting disordered systems. The exciton localization length (which corresponds to the thermal electronic conductance) is strongly enhanced by electron-electron interactions, while the localization length (pertaining to the charge conductance) is only slightly enhanced. This shows that the two particle delocalization mechanism widely discussed for the electron pair case is more efficient close to the Fermi energy for an electron-hole pair. The relevance to experiment is also discussed.

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Interacting electrons in random potentials are in the center of recent studies in mesoscopic systems because of their relevance to many different phenomena such as the Coulomb gap [1], persistent currents [2], the two-dimensional (2D) MIT (metal-insulator transition) [3], and delocalization of two particle states [2,4–6].

Although the subject of two particle state delocalization due to electron-electron (e-e) interaction has been the center of many recent studies [2], most of those studies concentrate on the situation of two particles in an empty band of a one-dimensional (1D) system. This is an idealized situation which is not very relevant to experimental systems. A more relevant situation, i.e. two excited electrons above the Fermi sea, was considered in Refs. [6,7]. In Ref. [7] it was shown that two electrons close to the Fermi energy show no enhancement in 1D systems. Nevertheless, it has been emphasized that the situation may be more favorable for higher dimensions [6], for which, up to now, only the empty band case was studied [8]. Recently it has been pointed out [9] that when the effect of the Coulomb gap is taken into account the two electron delocalization scenario becomes less likely.

In this letter we consider a different type of two particle delocalization, namely the delocalization of a tightly bound electron-hole pair (strongly bound excitons). This exciton is analogous to the classical compact electron-hole pair excitations discussed in Ref. [1], which can transfer energy across the system but not charge. This is different from most previous discussion of two particle delocalization which were concerned with the charge conductance of the system. Thus, delocalization of the electron-hole will manifest itself in the enhancement of the heat conductance of the disordered system, an effect which can be measured in the laboratory. Indeed, the relevance of the two particle delocalization scenario to electron-hole pairs has been noted by Imry [6]. In Ref. [9] it was suggested that not only is the two particle localization length enhancement relevant to an electron-hole pair, it is also much more effective than for the two electron case, because of the Coulomb enhancement of the exciton density. This scenario will be verified in this letter by explicit calculation of the localization length. Moreover, the existence of delocalized excitons may have interesting consequences for low temperature hopping conductance, which will be discussed in more

details after presenting the evidence for the exciton localization length enhancement.

Our study is based on the following interacting many-particle tight-binding Hamiltonian:

$$H = \sum_{k,j} \epsilon_{k,j} a_{k,j}^\dagger a_{k,j} - V \sum_{k,j} (a_{k,j+1}^\dagger a_{k,j} + a_{k+1,j}^\dagger a_{k,j}) + h.c + H_{int}, \quad (1)$$

where $\epsilon_{k,j}$ is the energy of a site (k, j) , chosen randomly between $-W/2$ and $W/2$ with uniform probability, and V is a constant hopping matrix element. The interaction Hamiltonian is given by:

$$H_{int} = U \sum_{k,j>l,p} \frac{a_{k,j}^\dagger a_{k,j} a_{l,p}^\dagger a_{l,p}}{|\vec{r}_{k,j} - \vec{r}_{l,p}|/b} \quad (2)$$

where $U = e^2/b$ and b is the lattice unit.

We consider $L_x \times L_y$ samples of size 3×2 , 3×3 , 3×4 and 3×5 with $M = 6, 9, 12, 15$ sites and $N = 2, 3, 4, 5$ electrons correspondingly (i.e., $1/3$ filling). The calculation of the electron transmission required also the calculation of the $N + 1$ electron Hamiltonian for each case. The $m \times m$ Hamiltonian (where $m = \binom{M}{N}$) matrix is numerically diagonalized and all the eigenvectors $|\Psi_l^N\rangle$ and eigenvalues E_l^N are obtained. The strength U of the interaction is varied between $0 - 30V$ and the disorder strength is chosen to be $W = 30V$. The results are averaged over 6000, 1000, 200, 25 different realizations of disorder for the $M = 6, 9, 12, 15$ samples.

The zero temperature tunneling density of state (TDOS) for the $N + 1$ electron is defined in the usual way [10]:

$$\nu(\varepsilon) = \sum_l |\langle \Psi_l^{N+1} | \sum_{k,j} a_{k,j}^\dagger | \Psi_0^N \rangle|^2 \delta(\varepsilon - (E_l^{N+1} - E_0^N)) \quad (3)$$

which for the non-interacting case will reproduce the single particle density of states above the Fermi energy. The averaged TDOS $\langle \nu(\varepsilon) \rangle = (0.4\Delta')^{-1} \int_{\varepsilon-0.2\Delta'}^{\varepsilon+0.2\Delta'} \langle \nu(\varepsilon') \rangle d\varepsilon'$ (here $\langle \dots \rangle$ stands for an average over realizations of disorder) for different values of interaction is presented in Fig. 1a. Since the distance to the many particle band edge B increases as function of the interaction strength U we rescale the single particle level spacing Δ to offset this trend. The rescaled “single particle” level spacing is defined as $\Delta' = B/N(M - N)$,

which is equal to Δ in the non-interacting case. For large values Δ' there is little influence of the interaction strength on $\nu(\varepsilon)$, while for small values of Δ' there is a change. While for $U = 0$ the TDOS is rather monotonous except for a remanent of the level repulsion at $\Delta' = 0$, there is a signature of the Coulomb gap [1] at $U = 30V$. Thus, the TDOS shows the expected behavior as function of the interaction strength.

We shall define a tightly bound exciton as the movement of an electron from its ground state position to a neighboring site, which may be expressed by the application of a creation operator $J_{k,j}^\dagger = J_{k,j}^{-x\dagger} + J_{k,j}^{+x\dagger} + J_{k,j}^{-y\dagger} + J_{k,j}^{+y\dagger}$ (where $J_{k,j}^{\pm x\dagger} = a_{k,j\pm 1}^\dagger a_{k,j}$ and $J_{k,j}^{\pm y\dagger} = a_{k\pm 1,j}^\dagger a_{k,j}$) on the ground state eigenvector. The overlap of an excited state with a state obtained out of the ground state by the creation of an exciton at site (k, j) is then given by $|\langle \Psi_l^{N+1} | J_{k,j}^\dagger | \Psi_0^{N+1} \rangle|^2$. One may also define the exciton density of state (EDOS)

$$\nu_E(\varepsilon) = \sum_l |\langle \Psi_l^{N+1} | \sum_{k,j} J_{k,j}^\dagger | \Psi_0^{N+1} \rangle|^2 \delta(\varepsilon - (E_l^{N+1} - E_0^{N+1})) \quad (4)$$

in an analogous way to the TDOS. The EDOS then describes the weight of a single tightly bound excitons at a given energy. The average EDOS $\langle \nu_E(\varepsilon) \rangle$ (calculated in the same way as the average TDOS) for different values of U is plotted in Fig. 1b. It is clear that the interaction strength influences the EDOS in a different way than the TDOS. There is no sign of the Coulomb gap, instead there is a monotonous enhancement of the EDOS, as one may expect from the classical theory of tight bound excitons which predicts a constant EDOS as function of ε [1].

The localization properties of a system manifest themselves in the transport behavior of the system. For a single particle system one may connect the localization length ξ to the transmission $t(\vec{r}, \vec{r}', \varepsilon) = \langle \vec{r} | (\varepsilon - H + i\eta)^{-1} | \vec{r}' \rangle$ via [11] $\xi(\varepsilon)^{-1} = \langle \ln |t(\vec{r}, \vec{r}', \varepsilon)| \rangle / |\vec{r} - \vec{r}'|$. In Ref. [12] a many particle Landauer formula connecting transmission and conductance for an interacting system coupled to external leads was developed. For the many particle case the transmission in the interacting region is given by

$$t(\vec{r}, \vec{r}', \varepsilon) = \sum_l \frac{\langle \Psi_l^{N+1} | a_{\vec{r}}^\dagger | \Psi_0^N \rangle \langle \Psi_0^N | a_{\vec{r}'} | \Psi_l^{N+1} \rangle}{\varepsilon - (E_l^{N+1} - E_0^N) + i\eta}, \quad (5)$$

where $\eta \rightarrow 0$ In the numerical calculation we assumed $\vec{r}$ and $\vec{r}'$ to correspond to the opposite corners of the sample, i.e., $\vec{r} = (1, 1)$ and $\vec{r}' = (1, L_y)$.

The heat transport (namely the exciton transport) can be probed for example by attaching leads which excite a tightly bound exciton at one point of the sample and absorbs it on another point. In this case the heat transmission is formulated as

$$t_h(\vec{r}, \vec{r}', \varepsilon) = \sum_l \frac{\langle \Psi_l^{N+1} | J_{\vec{r}}^\dagger | \Psi_0^{N+1} \rangle \langle \Psi_0^{N+1} | J_{\vec{r}'} | \Psi_l^{N+1} \rangle}{\varepsilon - (E_l^{N+1} - E_0^{N+1}) + i\eta}. \quad (6)$$

The localization length of the system are extracted from the numerical data in the following way: We calculate the average log of the (heat) transmission between the two corners of the sample for the low lying excitations $\langle \ln |t_{(h)}(\varepsilon)| \rangle = \langle \ln((2\Delta')^{-1} | \int_{\varepsilon-\Delta'}^{\varepsilon+\Delta'} t_{(h)}(\vec{r}, \vec{r}', \varepsilon') d\varepsilon' |) \rangle$. The results are presented in Figs. 2a for $\langle \ln |t_{(h)}(\varepsilon = \Delta')| \rangle$ and in 2b for $\langle \ln |t_{(h)}(\varepsilon = 2\Delta')| \rangle$. From the slope of $\langle \ln t \rangle$ vs. L_y one can deduce the localization length according to $\xi \propto L_y / \langle \ln t \rangle$ [11]. For the charge transmission we obtain the following localization length $\xi = 0.85b, 0.86b, 0.70b, 0.71b$ at $U = 0, 10V, 20V, 30V$ for $\varepsilon = \Delta'$ and $\xi = 1.01b, 1.20b, 1.08b, 0.95b$ at $U = 0, 10V, 20V, 30V$ for $\varepsilon = 2\Delta'$. Thus, the charge transmission is somewhat enhanced for weak interactions, but is suppressed for stronger interactions. This is in line with our expectations on the influence of the interaction on the charge conductance [13,14]. On the other hand for the heat transmission the exciton localization length $\xi_h = 0.33b, 0.47b, 0.59b, 0.59b$ corresponding to $U = 0, 10V, 20V, 30V$ for $\varepsilon = \Delta'$ and $\xi_h = 0.37b, 0.55b, 0.69b, 0.72b$ corresponding to $U = 0, 10V, 20V, 30V$ for $\varepsilon = 2\Delta'$. Thus, the heat transmission and the exciton localization length are significantly enhanced by the interactions.

Thus, low energy excitons show a significant enhancement of their localization length, while electrons in that region show only a moderate enhancement. This can be understood as the result of the fact that for electrons interacting via the Coulomb interaction the joint density of states of two electrons drastically decreases at small energies due to the Coulomb gap in the one-electron density of states. This leads to a suppression of the enhancement of the localization length which strongly depends on the two particle density of states. However,

for excitons, Coulomb effects increase the density of states making these arguments more plausible. This can be clearly seen for the stronger interaction strength ($U = 20V, 30V$) for which ξ_h are strongly enhanced, while ξ is suppressed compared to the non-interacting value. Also from a direct calculation of the two electron transmission, the suppression of the two electron localization length close to the Fermi energy is evident.

An enhancement of ξ_h will of course manifest itself in electronic thermal conduction measurements of disordered systems. For a case in which $\xi_h > \xi$, which has not been achieved for the parameters we have chosen in our model, but can not be out ruled for larger systems or at a different parameter range, interesting behavior may emerge. For example, it is quite possible that for $\xi \gg b$ the exciton localization length may become infinite so that the electronic conductivity is exponentially small while the electronic thermal conductivity changes as a power of temperature [15,9]. Another interesting effect in such a regime is the possibility that at low temperatures the delocalized excitons may assist electron hopping much more effectively than phonons [9,16,17]. This will result in a prefactor of the variable range hopping proportional or even equal to a universal value e^2/h . Such prefactors were observed in the QHE regime (see references and analysis in Refs. [16,17]) and recently at zero magnetic field [18].

In conclusion, we have shown that the two particle delocalization mechanism close to the Fermi energy is much more efficient for an electron-hole pair than for two electrons (or holes). This is a result of the enhancement of the exciton density of states near the Fermi energy by Coulomb interaction opposed to the suppression of the electronic density of states. This results in a large enhancement of the electronic thermal conductance while the conductance is only moderately enhanced.

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FIGURES

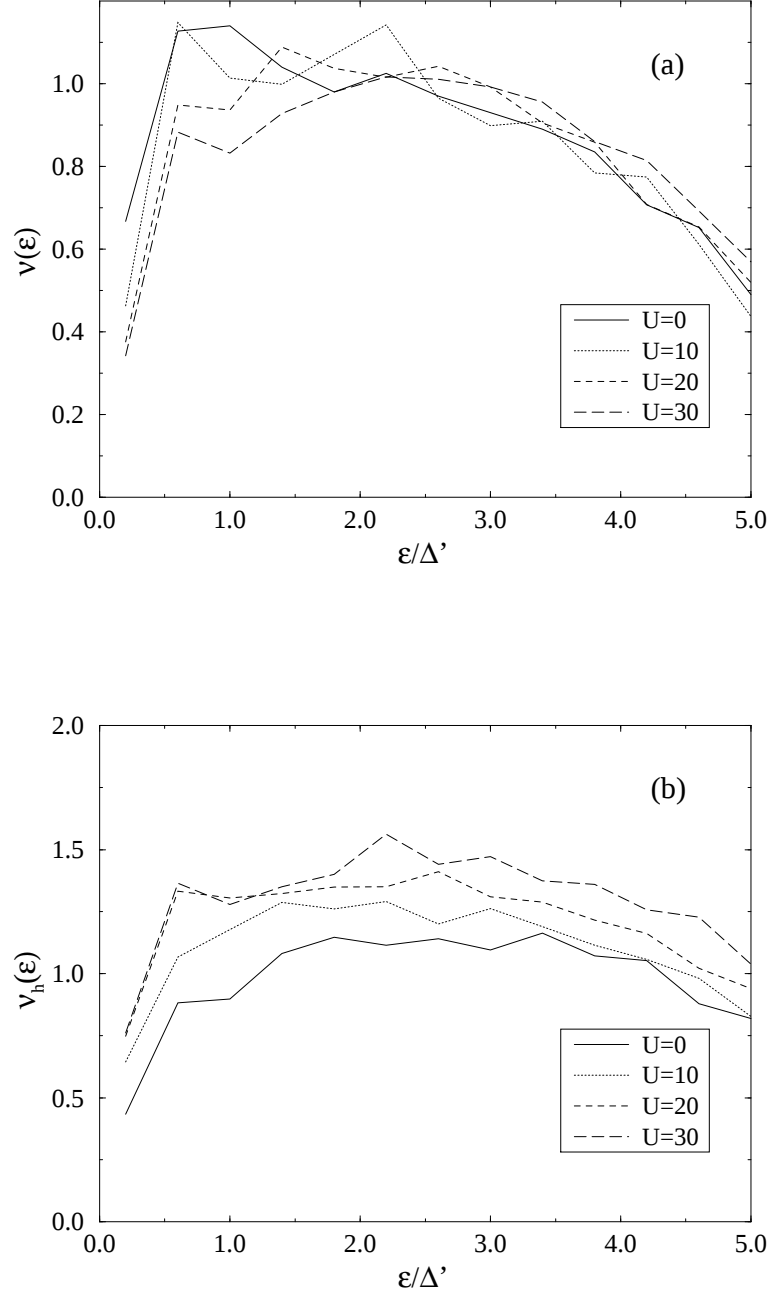


FIG. 1. The average transport density of state (a) and average exciton density of state (b) as function of the rescaled single electron level spacing of a 3×3 system for different values of interaction strength.

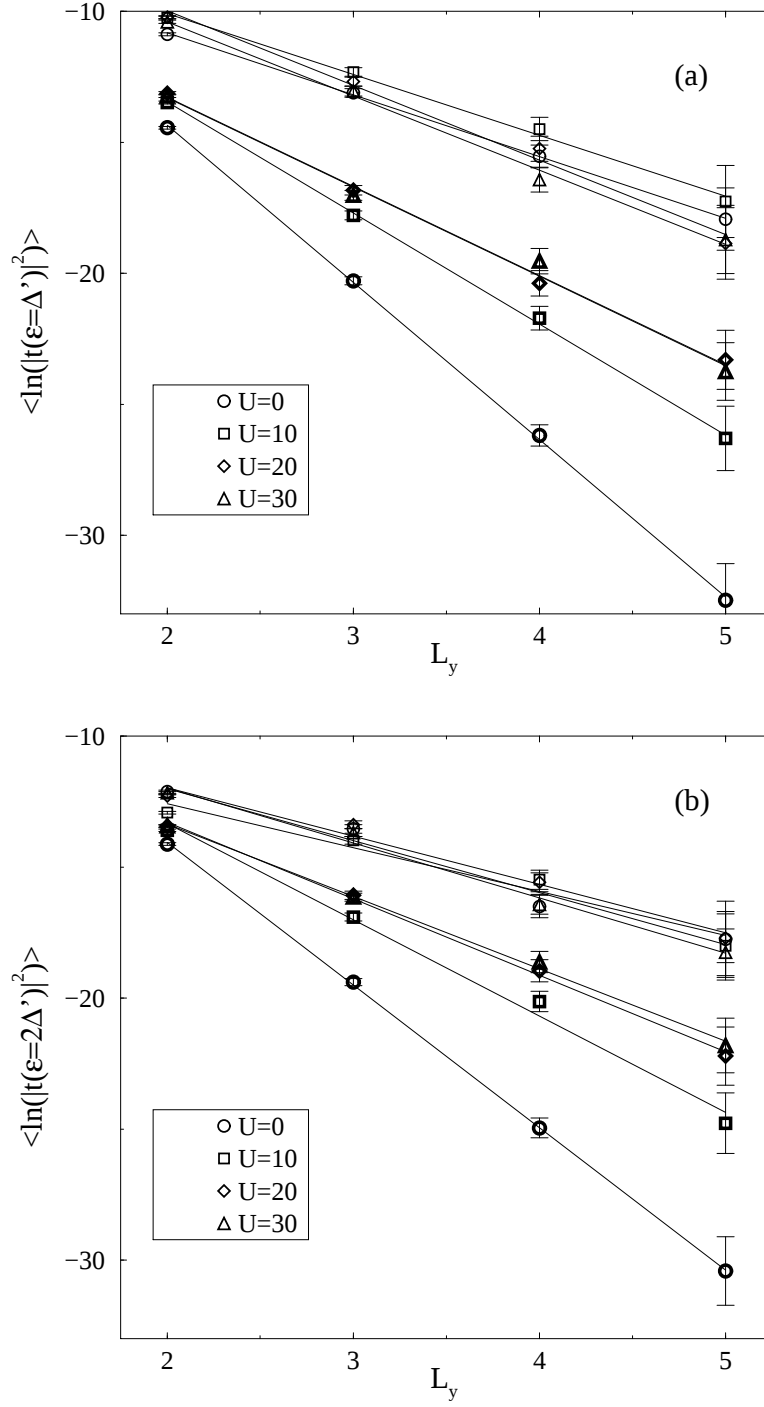


FIG. 2. The average log of the charge (regular symbols) and heat transmission (heavy symbols) as function of system length for different values of interaction strength. (a) $\varepsilon = \Delta'$ (b) $\varepsilon = 2\Delta'$